

L Number	Hits	Search Text	DB	Time stamp
2	83926	((resistivity near (less great\$6)) (low near resistance))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/01 15:31
3	19731	((resistivity near (less great\$6)) (low near resistance)) same (substrate pad base wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/01 15:33
4	9517	((((resistivity near (less great\$6)) (low near resistance)) same (substrate pad base wafer)) and electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/01 15:35
5	1230	((((resistivity near (less great\$6)) (low near resistance)) same (substrate pad base wafer)) and electrode) and ((buffer near layer) GaAs)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/01 15:36